1-Bit Gate Pulse Modulator

The NLHVQ011 is a 1-bit gate pulse modulator designed to translate logic voltages for TFT LCD panels for automotive applications. This part translates a low voltage logic input signal to an output voltage of 15 V to 38 V. In addition, the NLHVQ011 provides a user selectable delay and fall time on the high-to-low edge of the output signal. The delay and fall times are controlled by the magnitudes of the external and capacitor resistor, respectively.

Features

- Gate Pulse Modulation (GPM)
- AEC-Q100 Grade 1 Qualified
- Adjustable TFT LCD Flicker Compensation Circuitry
- Reduction of Coupling Effect Between Gate Line and Pixel
- Provides Power Sequencing Circuit for Gate Driver IC
- Wide Power Supply Operation: 15 V to 38 V
- Output Delay and Fall Time are Independently Adjustable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

• TFT LCDs

Important Information

• ESD Protection for All Pins: Human Body Model (HBM) > 3000 V

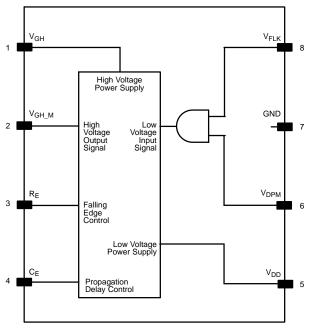
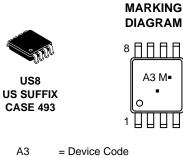


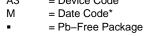
Figure 1. Block Diagram



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(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information on page 10 of this data sheet.

PIN DESCRIPTION

Pin	Pin Name	Pin Function	Comment
1	V _{GH}	Power Supply Input	V _{GH} = 15 to 38 V
2	V _{GH_M}	Output	This output directly drives the power supply of Gate Driver IC
3	R _E	R _E pin used to set the falling edge time (t _{fall})	The Delay time is programmed by connecting resistor $\rm R_{E}$ to $\rm V_{GH}$ and capacitor $\rm C_{E}$ to ground.
4	C _E	C _E pin used to set the propagation delay time (t _{phl})	
5	V _{DD}	Reference to input	The reference input pin is used to reduce flicker. The reference input voltage is as follows: $V_{DD} \le V_{GH} - 8.5 \text{ V}, V_{DD} = 0 \text{ to } 25 \text{ V}$
6	V _{DPM}	Signal input 1	V_{DPM} single input voltage is as follows: $V_{DPM} = 0 V$ to V_{GH} . The V_{DPM} pin is used to create a delay with the V_{GH} to prevent system latch–up. V_{DPM} also determines the time V_{GH} is ON.
7	GND	Ground	
8	V _{FLK}	Signal input 2	V_{FLK} single input voltage is as follows: V_{DPM} = 0 V to $V_{GH}.$ The V_{FLK} determines the ON/OFF time of the TFT LCD and is produced from LCD timing controller module.

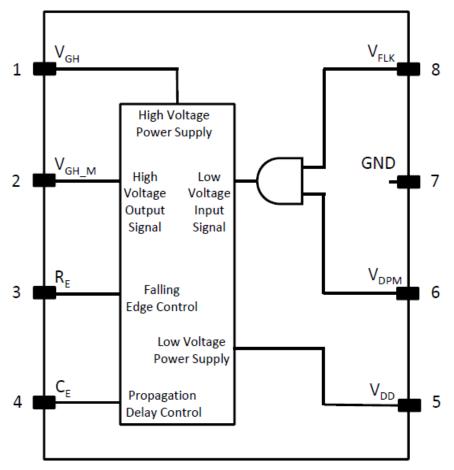


Figure 2. Block Diagram

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Condition	Value	Unit
V _{GH}	DC Supply Voltage		-0.5 to +40	V
V _{DD}	DC Supply Voltage		-0.5 to +40	V
V _{FLK}	Input Voltage V _{FLK}		-0.5 to +40	V
V _{DPM}	Input Voltage V _{DPM}		-0.5 to +40	V
I _{IK}	DC Input Diode Current		±50	mA
I _{OK}	DC Output Diode Current		±50	mA
Ι _Ο	DC Output Current		50	mA
I _{GH}	DC Supply Current Per Supply Pin		50	mA
PD	Power Dissipation		200	mW
ТJ	Junction Temperature		150	٥C
T _{STG}	Storage Temperature		-65 to +150	٥C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

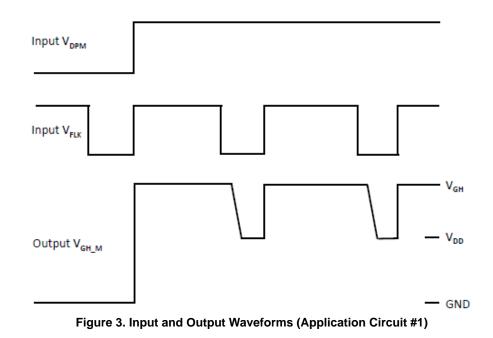
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _{GH}	DC Supply Voltage (Note 1)	$V_{GH} - V_{DD} \ge 8.5 V$	15	-	38	V
V _{DD}	DC Supply Voltage	$V_{DD} \le V_{GH} - 8.5 V$	0	-	25	V
V _{FLK}	Input Voltage V _{FLK}	V _{GH_M} = V _{GH} – 1.2 V	1.5	-	V _{GH}	V
V _{DPM}	Input Voltage V _{DPM}	V _{GH_M} = V _{DD} + 1.5 V	0	-	V _{GH}	V
T _A	Operating Temperature Range		-40	-	125	V
		C _E = 5 pF		0.2		
		C _E = 10 pF		0.4		
		C _E = 50 pF		0.6		
Δt / ΔV_{GH}	Safe V _{GH} Power–Up Slew Rate (Note 2)	C _E = 150 pF] _	0.7	- 1	μs / V
		C _E = 220 pF	1	0.8		
		C _E = 500 pF]	1.2		
		C _E = 1000 pF	1	2.2]	

Maximum recommended V_{GH} supply voltage guaranteed by design.
It is recommended that a ceramic or tantalum decoupling capacitor of 0.1 to 1 μF is used on the V_{GH} power supply voltage. The capacitor should be placed adjacent to the NLHVQ011 and connected between V_{GH} and Ground.

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V_{FLK_H}	FLK High Voltage	V _{GH_M} = V _{GH} – 1.6	1.5	-	V _{GH}	V
V_{FLK_L}	FLK Low Voltage	$V_{GH_M} = V_{DD} + 1.5$	0	-	0.5	V
V _{DPM_H}	DPM High Voltage	$V_{FLK} = 0 V, V_{GH_M} = V_{DD} - 0.2 V$	1.5	-	V _{GH}	V
V _{DPM_L}	DPM Low Voltage	V_{FLK} = 0 V, $V_{GH_M} \le 0.6$ V	0	-	0.5	V
I _{DPM}	DPM ON Current	$V_{FLK} = 3 V, V_{GH_M} = V_{GH}$	0.2	0.4	2	mA
R _C	R _C (Resistor of V _{DPM} pin)	$\label{eq:VGH} \begin{array}{l} V_{GH} = 22 \ V, \ R_C \approx \left(V_{GH} - 0.9 \right) / \\ I_{DPM} \ (Application \ Circuits \ 2 \ and \ 3) \end{array}$	10	45	100	kΩ
V _{GH_M, H}	Output High Voltage	I _O = 10 mA	V _{GH} – 1.6	V _{GH} – 0.7	-	V
V _{GH_M, R}	Output Reset Voltage	$V_{\text{DPM}} = 0 \text{ V}, V_{\text{FLK}} = 3 \text{ V}$			0.6	V
		$V_{\text{DPM}} = 0 \text{ V}, V_{\text{FLK}} = 0 \text{ V}$	1 -	-		V
V _{GH_M, L}	Output Low Voltage	$V_{DPM} = 3 V, V_{FLK} = 0 V,$ $I_O = -1 m A$	V _{DD} – 0.2	V _{DD} + 0.3	V _{DD} + 0.8	V
I _{GH}	Power Supply Input Current	$V_{GH} = 35 \text{ V}, V_{DD} = 15 \text{ V}, V_{FLK} = V_{DPM} = 3.3 \text{ V}, I_O = 0$	-	3.5	-	mA
I _{DD}	Reference Input Current	V _{GH} = 35 V, V _{DD} = 15 V, V _{FLK} = 0 V, V _{DPM} = 3.3 V, I _O = 0	-	40	-	μΑ

ELECTRICAL CHARACTERISTICS (V _{GH} = 20 V, V _{DD} = 10 V, V _{DPM} = 2.2 V, V _{FLK} = 2.2 V, V _{GH} - V _{DD} \ge 8.5 V, T _a = 25 °C, unless the second s	i
otherwise noted.)	



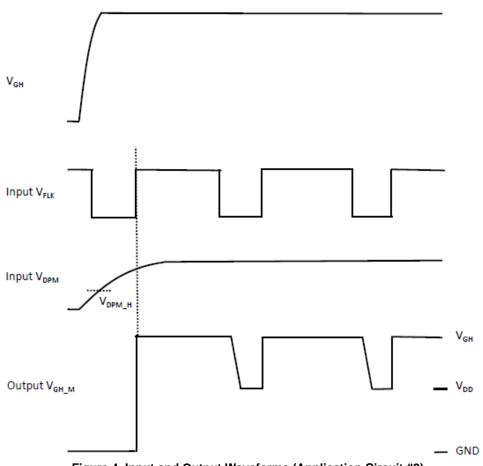


Figure 4. Input and Output Waveforms (Application Circuit #2)

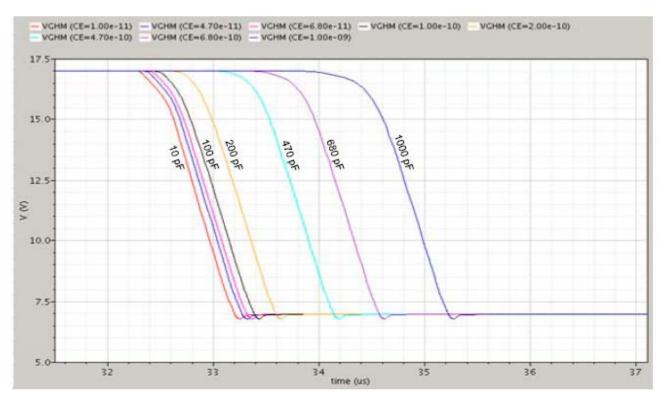


Figure 5. V_{GH_M} Output Propagation Delay (t_{phl}) is controlled by C_E (Application Circuit #1, V_{GH} = 18 V, V_{DD} = 7 V, R_E = 3.9 k Ω , R_L = 15 k Ω , C_L = 220 pF, T_a = 25 °C)

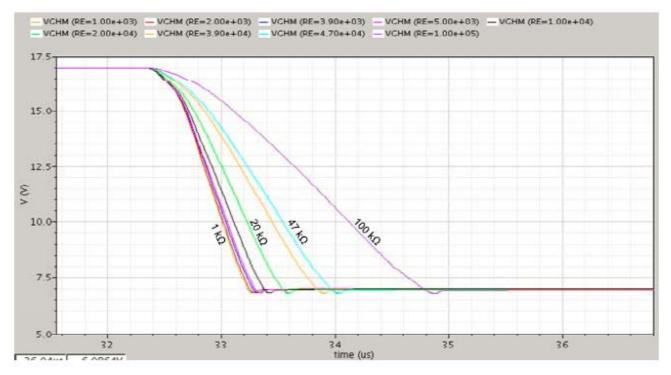
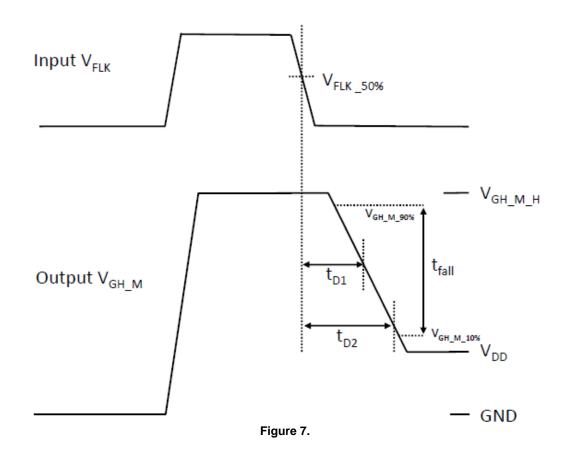


Figure 6. V_{GH_M} Output Transition Falling Edge (t_{fall}) is controlled by R_E (Application Circuit #1, V_{GH} = 18 V, V_{DD} = 7 V, C_E = 47 pF, R_L = 15 k Ω , C_L = 220 pF, T_a = 25 °C)



Definition of Delay Time

 $t_{D1} = Delay Time 1 \ (t_{D_50-50}) = V_{FLK_50\%} \ to \ [V_{DD} + ((V_{GH_M_H}) - V_{DD}) \ x \ 0.50)] \\ t_{D2} = Delay Time 2 \ (t_{D_50-15}) = V_{FLK_50\%} \ to \ [V_{DD} + ((V_{GH_M_H}) - V_{DD}) \ x \ 0.15)] \\ t_{fall} = 90 - to - 10\% \ Fall Time = [V_{DD} + ((V_{GH_M_H}) - V_{DD}) \ x \ 0.90)] - [V_{DD} + ((V_{GH_M_H}) - V_{DD}) \ x \ 0.10)]$

DELAY TIME CHARACTERISTICS

(Application Circuit #1, V_DPM = 3 V, V_{FLK} = 3 V, R_E = 15 k\Omega, R_L = 15 k Ω , C_L = 220 pF, T_A = 25°C)

Parameter	Test Condition	Тур	Unit
	V_{GH} = 17 V, V_{DD} = 6.7 V, C_{E} = 100 pF	2.4	μs
	V_{GH} = 17 V, V_{DD} = 6.7 V, C_{E} = 240 pF	2.8	μs
Delay Time 2 (t _{D_50–15})	V_{GH} = 22.4 V, V_{DD} = 10 V, C_{E} = 91 pF	2.3	μs
Delay Time 2 (1D_50-15)	V_{GH} = 22 V, V_{DD} = 10 V, C_{E} = 220 pF	2.8	μs
	V_{GH} = 25.4 V, V_{DD} = 15.4 V, C_E = 56 pF	2.4	μs
	V_{GH} = 25.4 V, V_{DD} = 15.4 V, C_E = 130 pF	2.5	μs

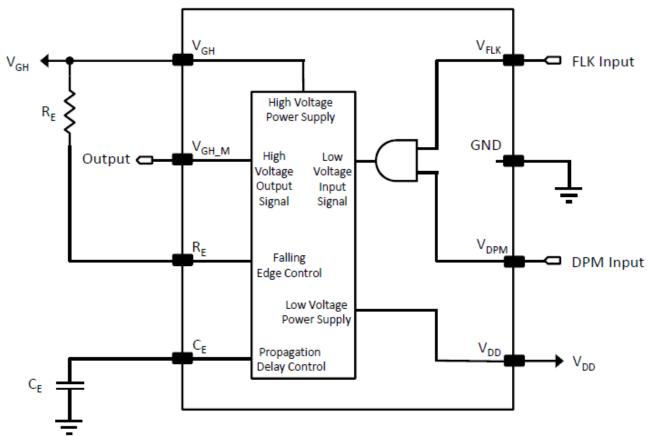
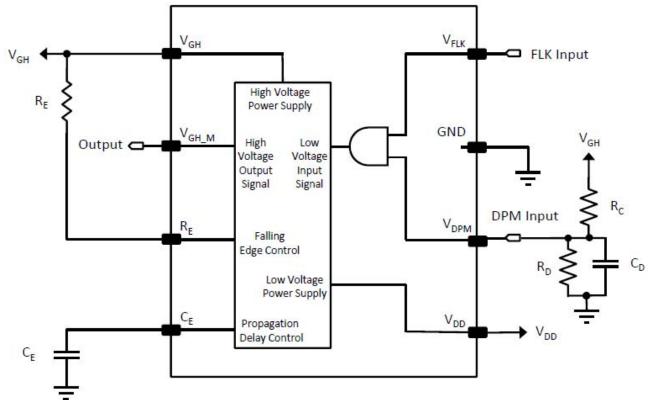
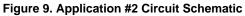


Figure 8. Application #1 Circuit Schematic

Notes:

1. V_{DPM} can rise only after V_{GH} is valid.





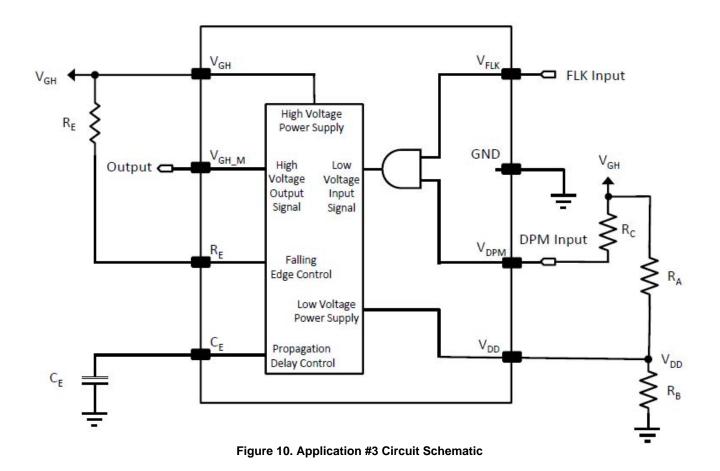
Notes:

- 1. V_{DPM} is produced by a Low Pass Filter (LPF) on V_{GH} pin with R_C and C_D .
- 2. R_D is a V_{DPM} pull-down resistor.

V _{GH} (V)	V _{DD} (V)	C _D (μF)	R _D (kΩ)	R _C (kΩ)	V _{GH_M} ON Delay Time (when V _{GH} ON) t _{on} (ms)	V _{DPM} Pin Discharge Time (when V _{GH} OFF) t _{off} (ms)
		1	15	50	17.9	3.4
22	12	1	1.5	20	5.5	1.4
		1	0.620	10	1.7	0.74

APPLICATION 2: FUNCTION DESCRIPTION

Name	Comment	Function	
R _C	R_{C} and C_{D} determines the time when the V_{DPM} pin is charged.		
CD	charged.	t_{on} = Time when V_{GH_M} is high	
R _D	R_{D} determines the time when the V_{DPM} pin is discharged.	t_{off} = Time when V _{DPM} pin is fully discharged	



APPLICATION 3: FUNCTION DESCRIPTION

Name	Comment	Function
R _A	$\rm R_A$ and $\rm R_B$ set the $\rm V_{DD}$ voltage.	$V_{DD} = V_{GH} x (R_B / (R_A + R_B))$
R _B		
R _C	R_C determines the voltage that V_DPM pin becomes high.	

Notes:

1. V_{DPM} produced by external R_C and internal R and C.

2. V_{DD} created from external resistors R_A and R_B .

3. V_{GH} should be higher than 18 V to meet $V_{DPM_{-H}}$.

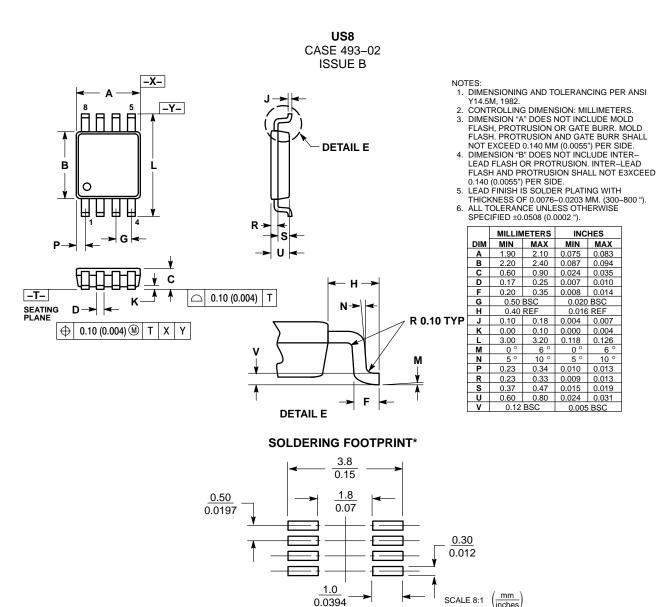
4. $R_A = 15 \text{ k}\Omega$, $R_B = 10 \text{ k}\Omega$, $R_C = 45 \text{ k}\Omega$, $R_E = 15 \text{ k}\Omega$, $R_L = 15 \text{ k}\Omega$, $C_E = 220 \text{ pF}$, $C_L = 100 \text{ pF}$

DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Shipping [†]
NLHVQ011USG	US8 (Pb–Free)	3000 / Tape & Reel

⁺For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

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